

Preliminary **TSM6970D** 20V Dual N-Channel MOSFET w/ESD Protected

PRODUCT SUMMARY



Pin Definition: 1. Di 2. S

3. S 4. Gate 1 5. Gate 2

rain 1	8. Drain 2
ource 1	7. Source 2
ource 1	6. Source 2

V _{DS} (V)	R _{DS(on)} (mΩ)	I _D (A)				
	21 @ V _{GS} = 4.5V	8				
20	25 @ V _{GS} = 2.5V	7				
	33 @ V _{GS} = 1.8V	6				

Features

- Advance Trench Process Technology •
- High Density Cell Design for Ultra Low On-resistance •
- ESD Protect 2KV •

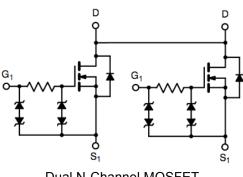
Application

- Load Switch
- PA Switch •

Ordering Information

Part No.	Package	Packing
TSM6970DCA RV	TSSOP-8	3Kpcs / 13" Reel

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V _{GS}	±8	V	
Continuous Drain Current, V _{GS} @4.5V		Ι _D	8	А	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	30	А	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	2.5	А	
Meximum Device Discipation	Ta = 25°C	D	2	W	
Maximum Power Dissipation	Ta = 70°C	P _D	1.28		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	RƏ _{JC}	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	RƏ _{JA}	62.5	°C/W

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, $t \le 5$ sec.



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Electrical Specifications

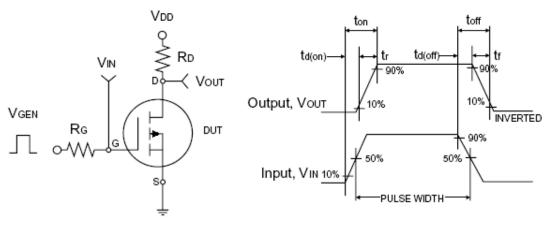
Parameter	Conditions	Symbol	Min	Тур	Мах	Unit
Static						
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_{D} = 250uA	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \text{uA}$	V _{GS(TH)}	0.4		1	V
Gate Body Leakage	V_{GS} = ±8V, V_{DS} = 0V	I _{GSS}			±10	uA
Zero Gate Voltage Drain Current	V_{DS} = 16V, V_{GS} = 0V	I _{DSS}			1	uA
On-State Drain Current	V_{DS} =5V, V_{GS} = 4.5V	I _{D(ON)}	10			А
	V _{GS} = 4.5V, I _D = 8A			18	21	mΩ
Drain-Source On-State Resistance	V _{GS} = 2.5V, I _D = 7A	R _{DS(ON)}		21	25	
	V _{GS} = 1.8V, I _D = 6A			26	33	
Forward Transconductance	$V_{DS} = 5V, I_{D} = 8A$	g _{fs}		13		S
Diode Forward Voltage	I _S = 2.5A, V _{GS} = 0V	V _{SD}			1.7	V
Dynamic ^b				_	_	-
Total Gate Charge	$V_{DS} = 10V, I_D = 8A,$ $V_{GS} = 4.5V$	Qg		13.8		
Gate-Source Charge		Q _{gs}		4.1		nC
Gate-Drain Charge	v _{GS} - 4.5 v	Q_gd		5.6		
Input Capacitance		C _{iss}		1160		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	C _{oss}		104		pF
Reverse Transfer Capacitance	- f = 1.0MHz	C _{rss}		29		
Switching ^c						
Turn-On Delay Time	$V_{DD} = 10V,$ $I_{D} = 1A, V_{GEN} = 4.5V,$ $D_{D} = 20$	t _{d(on)}		140	200	
Turn-On Rise Time		t _r		210	250	20
Turn-Off Delay Time		t _{d(off)}		3700	4800	nS
Turn-Off Fall Time	$-R_{\rm G}=3\Omega$	t _f		2000	2600	

Notes:

a. pulse test: PW ≤300µS, duty cycle ≤2%

b. For DESIGN AID ONLY, not subject to production testing.

b. Switching time is essentially independent of operating temperature.



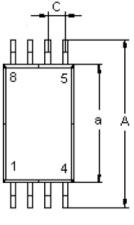
Switching Test Circuit

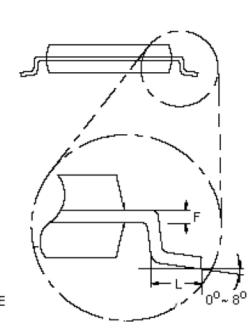
Switchin Waveforms



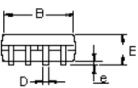
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TSSOP-8 Mechanical Drawing





TSSOP-8 DIMENSION					
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
А	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
С	0.65	(typ) 0.025 (ty		5 (typ)	
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
F	0.127		0.005		
L	0.50	0.70	0.020 0.028		





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